

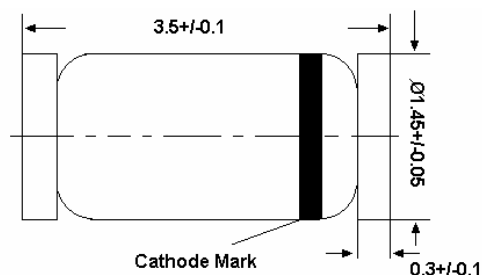
LL700, LL700A

SILICON EPITAXIAL PLANAR TYPE SCHOTTKY BARRIER DIODES

for Ordinary Wave Detection
for Super High Speed Switching

Features

- Low forward rise voltage (V_F) and satisfactory wave detection efficiency (η)
- Small temperature coefficient of forward characteristic
- Extremely low reverse current I_R



Glass case MiniMELF
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Rating	Unit
Reverse Voltage (DC)	V_R	15	V
		30	
Peak Reverse Voltage	V_{RM}	15	V
		30	
Forward Current (DC)	I_F	30	mA
Peak Forward Current	I_{FM}	150	mA
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_S	-55 to +125	$^\circ\text{C}$

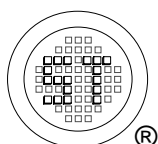
Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward Voltage (DC)	V_{F1}	$I_F = 1\text{mA}$	-	-	0.4	V
	V_{F2}	$I_F = 30\text{mA}$	-	-	1	
Reverse Current (DC)	I_R	$V_R = 15\text{V}$	-	-	100	nA
		$V_R = 30\text{V}$	-	-	150	
Terminal Capacitance	C_t	$V_R = 1\text{V}, f = 1\text{MHz}$	-	1.3	-	pF
Reverse Recovery Time*	t_{rr}	$I_F = I_R = 10\text{mA}$ $I_{rr} = 1\text{mA}, R_L = 100\Omega$	-	1	-	ns
Detection Efficiency	η	$V_{in} = 3V_{(peak)}, f = 30\text{MHz}$ $R_L = 3.9\text{k}\Omega, C_L = 10\text{pF}$	-	60	-	%

Note: (1) Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on the charge of a human body and the leakage of current from the operating equipment.

(2) Rated input / output frequency: 2,000MHz.

(3) *: t_{rr} measuring instrument



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ISO/TS 16949 : 2002
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